

40V P-Channel Enhancement Mode MOSFET

Description

The CP40P04D6 uses advanced trench technology to provide excellent $R_{DS(ON)}$, This device is suitable for use as a load switch or in PWM applications.

General Features

- ◆ $V_{DS} = -40V$, $I_D = -40A$
 $R_{DS(ON)}(Typ.) = 9m\Omega$ @ $V_{GS} = -10V$
 $R_{DS(ON)}(Typ.) = 13m\Omega$ @ $V_{GS} = -4.5V$
- ◆ High power and current handling capability
- ◆ Lead free product is acquired
- ◆ Surface mount package
- ◆ 150 °C operating temperature
- ◆ 100% UIS tested

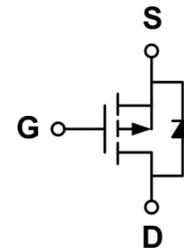
Application

- ◆ PWM applications
- ◆ Load switch
- ◆ Uninterruptible power supply

Package

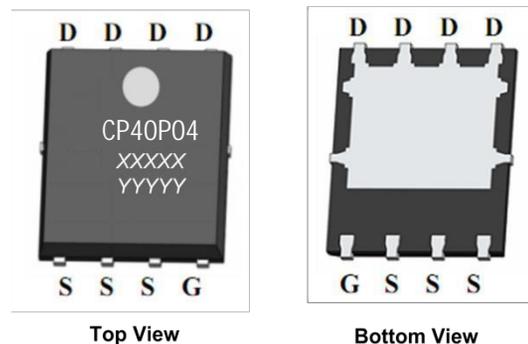
- ◆ PDFN5*6-8L-A

Schematic diagram



Marking and pin assignment

PDFN5*6-8L-A



XXXXX—Wafer Information
 YYYYY—Quality Code

Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
CP40P04D6-G	-55°C to +150°C	PDFN5*6-8L-A	5000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

parameter	symbol	limit	unit	
Drain-source voltage	V_{DS}	-40	V	
Gate-source voltage	V_{GS}	±20	V	
Continuous Drain Current	I_D	TC=25°C	-40	A
		TC=70°C	-36	
Pulsed Drain Current	I_{DP}	-120	A	
Avalanche energy (Tj=25°C, VDD=30V, VG=10V, L=0.5mH, Rg=50Ω)	E_{AS}	45	mJ	
Power Dissipation	P_D	TC=25°C	31	W
		TC=70°C	20	
Operating junction Temperature range	T_j	-55—150	°C	

Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	-40	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-40V, V _{GS} =0V	-	-	-1	μA
		T _J =85°C	-	-	-10	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.85	-2.5	V
Drain-source on-state resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-20A	-	9	12	mΩ
		V _{GS} =-4.5V, I _D =-15A	-	13	16	
On Status Drain Current	I _{D(ON)}	V _{DS} =-20V, V _{GS} =-10V	-40	-	-	A
Diode Characteristics						
Diode Forward Voltage	V _{SD}	I _{SD} =-20A, V _{GS} =0V	-	-0.7	-1	V
Diode Continuous Forward Current	I _S		-	-40	-	A
Reverse Recovery Time	t _{rr}	I _F =-20A,	-	24	-	ns
Reverse Recovery Charge	Q _{rr}	di/dt=-100A/us	-	16	-	
Dynamic Characteristics						
Gate Resistance	R _G	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	6.5	-	Ω
Input capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =-20V f=1.0MHz	-	3761	-	pF
Output capacitance	C _{OSS}		-	302	-	
Reverse transfer capacitance	C _{RSS}		-	275	-	
Turn-on delay time	t _{D(ON)}	V _{GS} =-10V, V _{DS} =-40V, R _L =3Ω, I _D =-20A, R _G =2.5Ω	-	11	-	ns
Turn-on Rise time	t _r		-	9.4	-	
Turn-off delay time	t _{D(OFF)}		-	24	-	
Turn-off Fall time	t _f		-	12	-	
Total gate charge	Q _g	V _{GS} =-10V, I _D =-20A V _{DS} =-20V	-	73	-	nC
Gate-source charge	Q _{gs}		-	12.5	-	
Gate-drain charge	Q _{gd}		-	15	-	

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit	
Maximum Junction-to-Ambient ^A	≤ 10s	R _{θJA}	29	34	°C/W
Maximum Junction-to-Ambient ^A	Steady-State		56		
Maximum Junction-to-Lead ^B	Steady-State	R _{θJC}	3.2	4	

A: The value of R_{θJA} is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

Typical Performance Characteristics

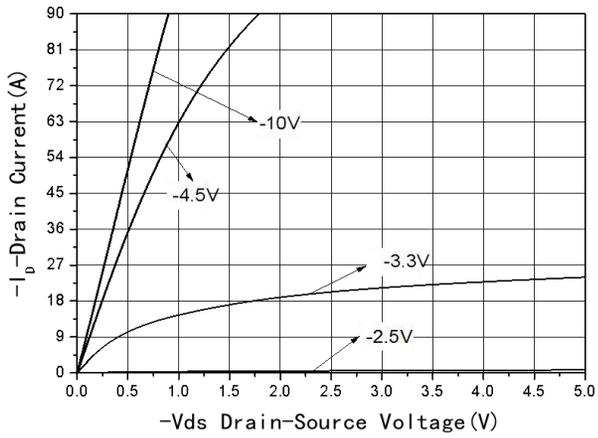


Fig1 Output Characteristics

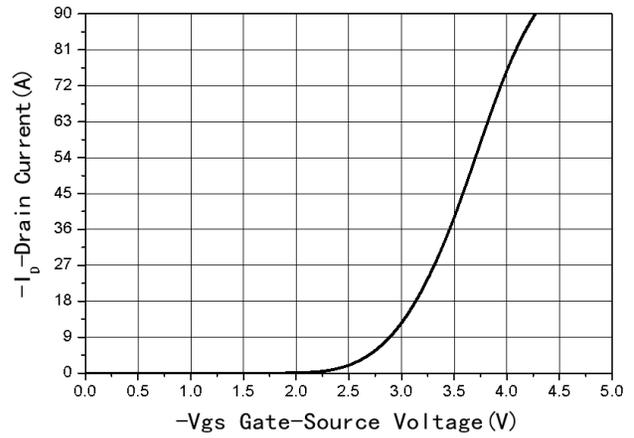


Fig2 Transfer Characteristics

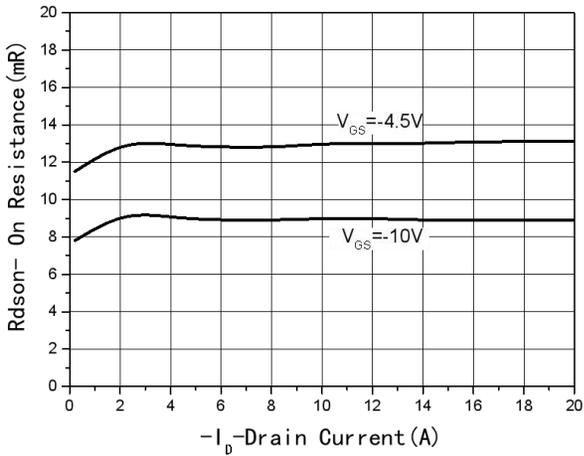


Fig3 Rdson-Drain current

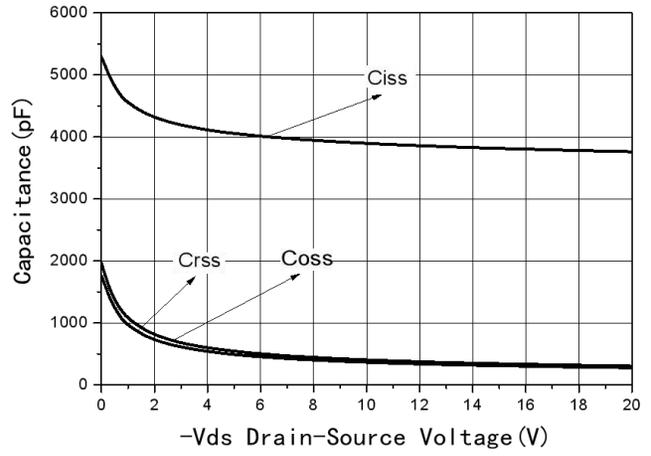


Fig4 Capacitance vs Vds

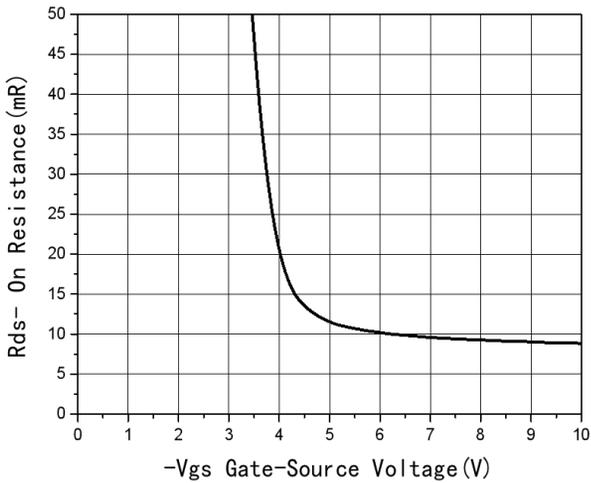


Fig5 Rdson-Gate Drain voltage

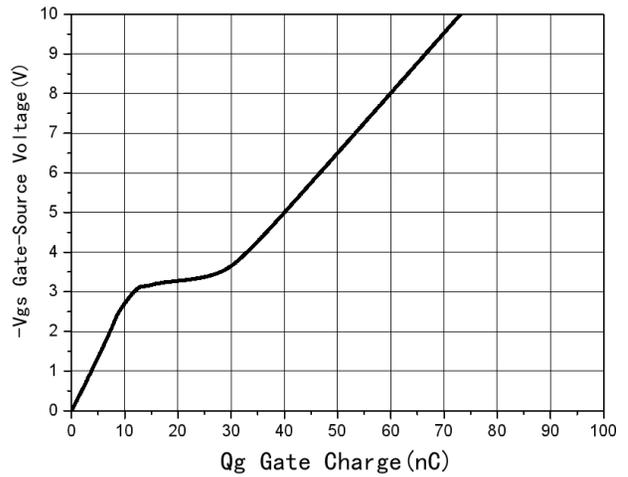
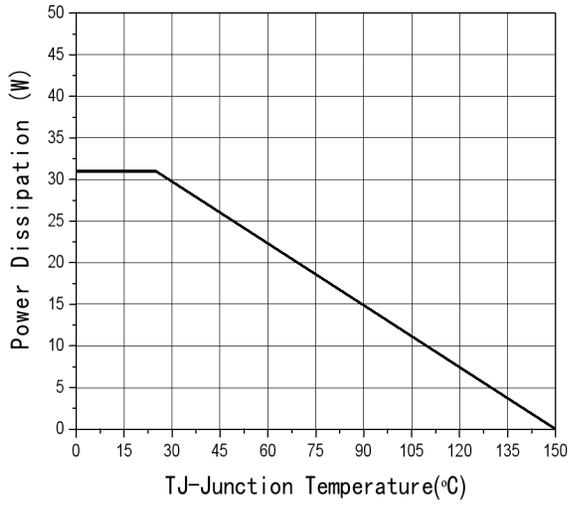
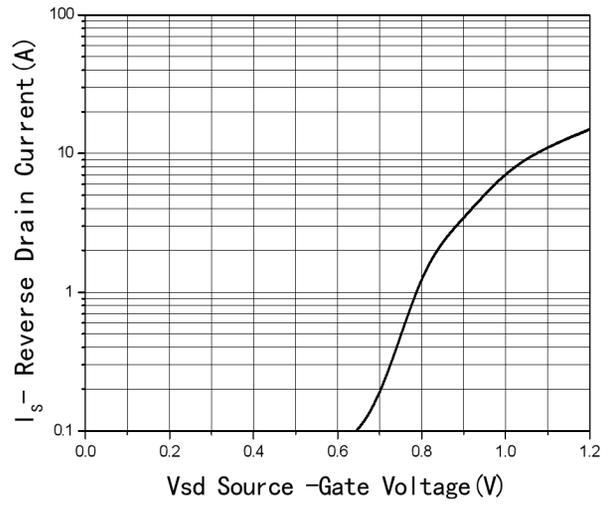
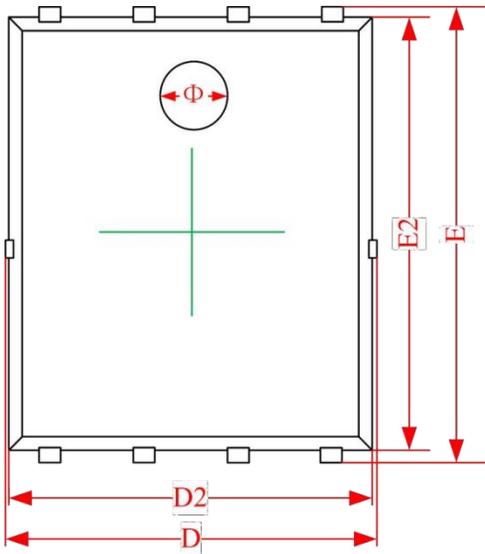
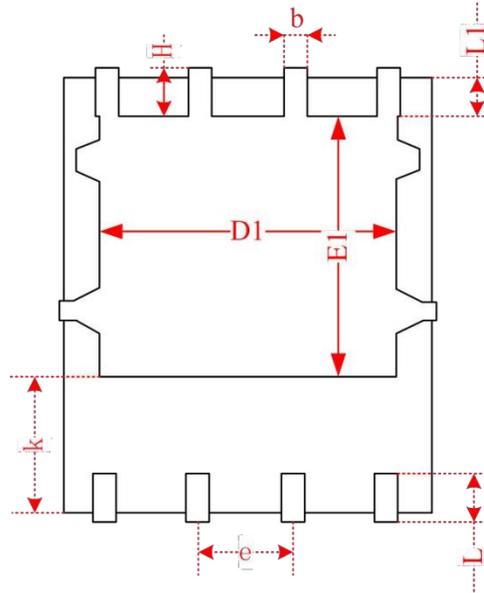
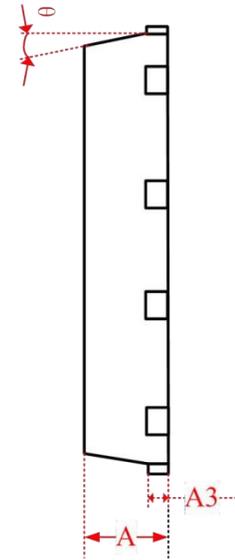


Fig6 Gate Charge

**Fig7 Power De-rating****Fig8 Source-Drain Diode Forward**

Package Information

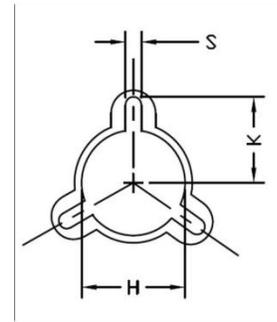
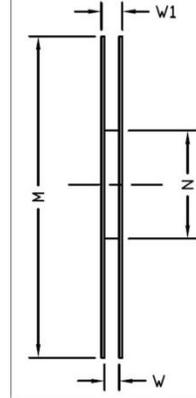
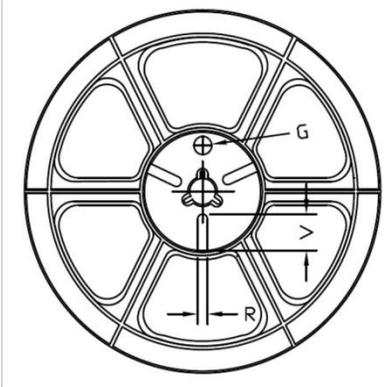
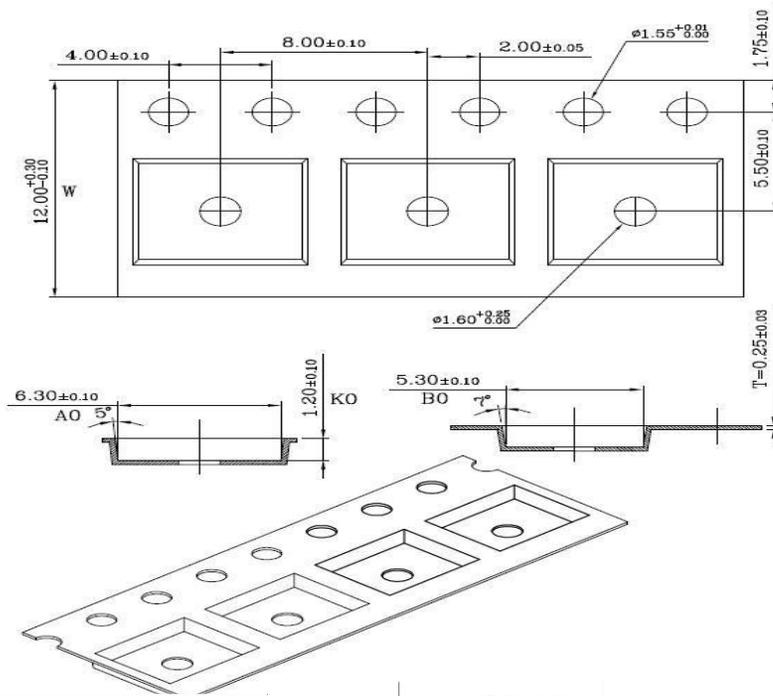
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Top View

Bottom View

Side View


SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.870	0.900	0.930	0.034	0.035	0.036
A3	0.203REF.			0.008REF.		
D	4.944	5.020	5.096	0.195	0.198	0.201
E	5.974	6.050	6.126	0.235	0.238	0.241
D1	3.910	4.010	4.110	0.154	0.158	0.162
E1	3.375	3.475	3.575	0.133	0.137	0.141
D2	4.870	4.900	4.930	0.192	0.193	0.194
E2	5.720	5.750	5.780	0.226	0.227	0.228
k	1.190	1.290	1.390	0.047	0.051	0.055
b	0.350	0.380	0.410	0.014	0.015	0.016
e	1.270TYP.			0.050TYP.		
L	0.559	0.635	0.711	0.022	0.025	0.028
L1	0.424	0.500	0.576	0.017	0.020	0.023
H	0.574	0.650	0.726	0.023	0.026	0.029
θ	10°	11°	12°	10°	11°	12°
Φ	1.150	1.200	1.250	0.045	0.047	0.049

Tape and Reel

- PDFN5*6-8L



Tape Size	Reel Size	M	N	W	W1	H	K	S	G	R	V
12mm	Φ330	Φ330.00 ±0.50	Φ97.00 ±0.30	13.00 ±0.30	17.40 ±1.00	Φ13.00 ±0.5	10.6	2.00 ±0.50	—	—	—

Unit Per Reel:
4000pcs

